风光欣技术资料

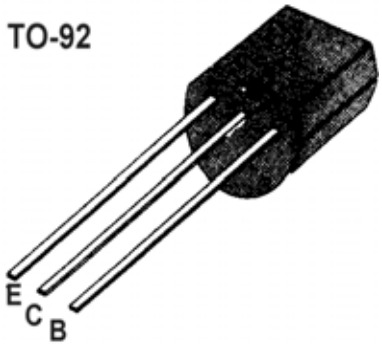
A1309

—PNP silicon —

■■**APPLICATION**：GENERAL PURPOSE APPLICATION.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	400				V_{CE}= -10V，Ic= -2mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -30V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-30			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-25			V	Ic= -1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	Ic= -100mA，I_B= -10mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	Ic= -100mA，I_B= -10mA
Gain bandwidth product	f_T	40			MHz	Ic= -1mA，V_{CE}= -10V
Common Base Output Capacitance	Cob		4	7	PF	V_{CB}= -10V，I_E=0，f = 1MHz
Power Gain	G_P		1.0	10	dB	V_{CE}= -6V,Ic= -0.1mA,f= 1MHz,Rg=10KΩ

■■h_{FE} **Classification**

Classification	O	Y
h_{FE}	≥400	